

Inventor: Arup Bhattacharyya

Title: Semiconductor Devices, and Electronic Systems Comprising
Semiconductor Devices

Assignee: Micron Technology, Inc.

INFORMATION DISCLOSURE STATEMENT
PURSUANT TO 37 C.F.R. " 1.56, 1.97 AND 1.98

In compliance with 37 C.F.R. §§ 1.56, 1.97 and 1.98, your attention is directed to the United States patents and other references listed on the attached Form PTO-1449. No admission is made regarding whether all the submitted references are prior art.

The listed references were cited by, or submitted to, the Office in the parent, co-pending application of the above-identified application. The above-identified application is a continuation application of co-pending application Serial No. 10/364,710, filed February 10, 2003. Such prior disclosure is sufficient for the above-identified application as far as copies of the references are concerned. 37 C.F.R. § 1.98(d) and MPEP § 609(2).

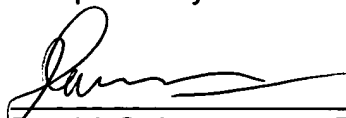
Citation of these references is respectfully requested.

Dated: _____

2/17/04

Respectfully submitted,

By: _____


David G. Latwesen, Ph.D.
Reg. No. 38,533

MyeSrsForm PTO-1449		U.S. DEPARTMENT OF COMMERCE PATENT AND TRADEMARK OFFICE		ATTY. DOCKET NO. MI22-2506		PRIORITY SERIAL NO. 10/364,710	
LIST OF ART CITED BY APPLICANT (Use several sheets if necessary)				APPLICANT Arup Bhattacharyya			
				PRIORITY FILING DATE February 10, 2003		GROUP Unknown	
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<p>*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.</p>							

Form PTO-1449		U.S. DEPARTMENT OF COMMERCE PATENT AND TRADEMARK OFFICE		ATTY. DOCKET NO. MI22-2163	SERIAL NO. 10/364,710
LIST OF ART CITED BY APPLICANT (Use several sheets if necessary)				APPLICANT Arup Bhattacharyya	
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LIST OF ART CITED BY APPLICANT (Use several sheets if necessary)				APPLICANT Arup Bhattacharyya	
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LIST OF ART CITED BY APPLICANT (Use several sheets if necessary)				APPLICANT Arup Bhattacharyya			
				PRIORITY FILING DATE February 10, 2003		GROUP Unknown	
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*Examiner Initial	Document Number	Date	Name	Class	Subclass	Filing Date If Appropriate	
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	AF						
	AG						
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	AI						
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FOREIGN PATENT DOCUMENTS							
	Document Number	Date	Country	Class	Subclass	Translation	
						Yes	No
	AL						
	AM						
	AN						
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